

MEDIUM POWER SILICON MICROWAVE TRANSISTOR

PRODUCT DATA SHEET

FEATURES:

- High Gain Bandwidth Product
 $f_t = 8 \text{ GHz typ @ } I_C = 14 \text{ mA}$
- High Gain
 $|S_{21}|^2 = 14.2 \text{ dB @ } 1.0 \text{ GHz}$
 $8.2 \text{ dB @ } 2.0 \text{ GHz}$

- Dice, Plastic, Hermetic and Surface Mount packages available

PERFORMANCE DATA:

- Electrical Characteristics ($T_A = 25^\circ\text{C}$)

DESCRIPTION AND APPLICATIONS:

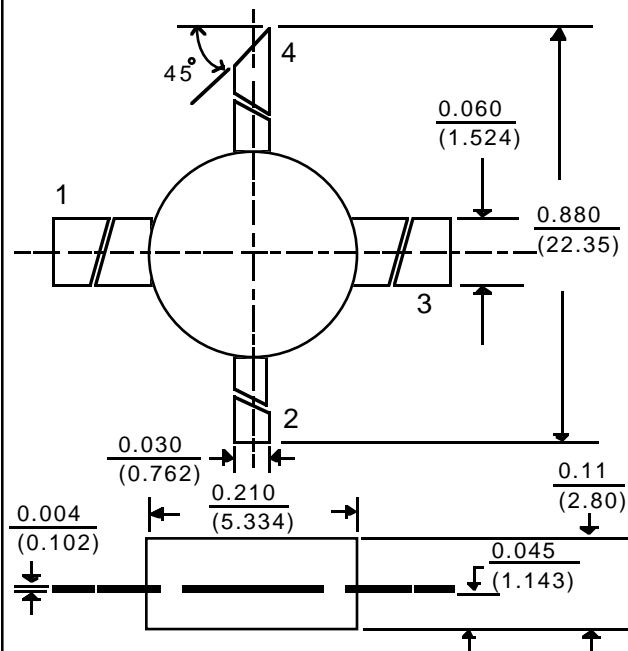
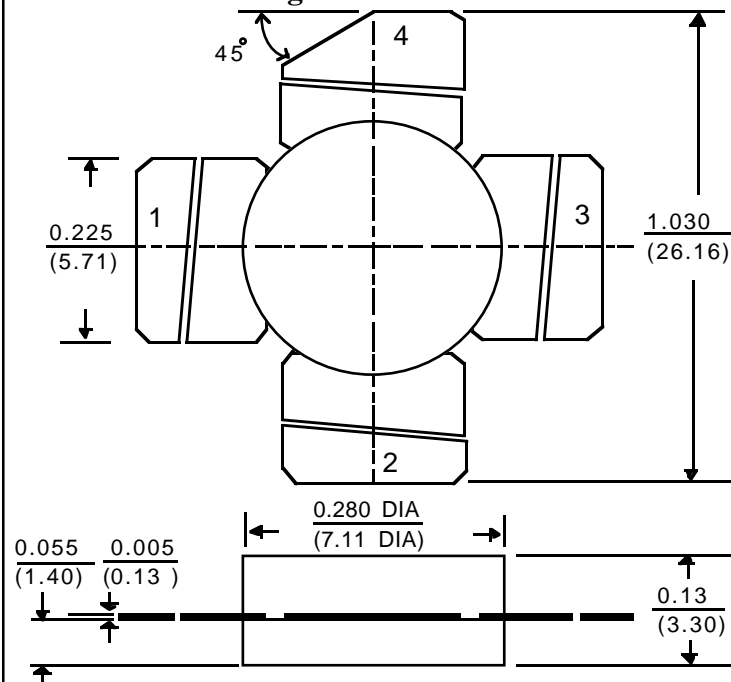
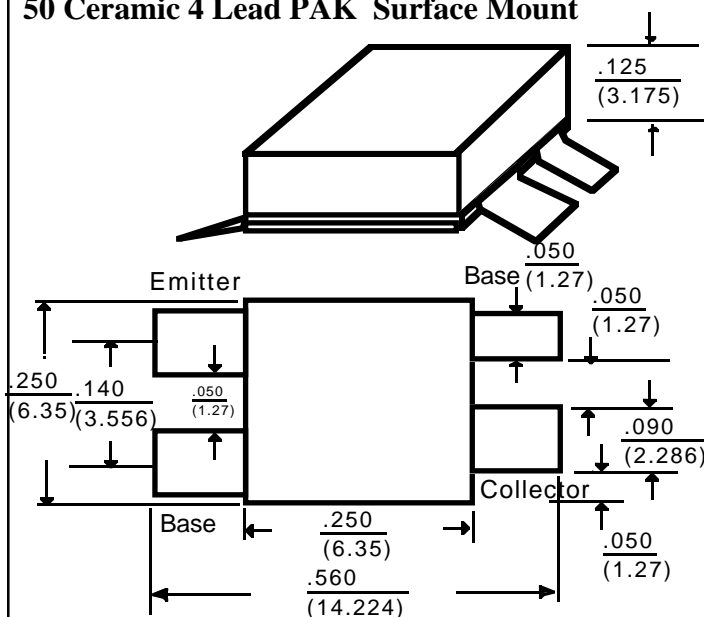
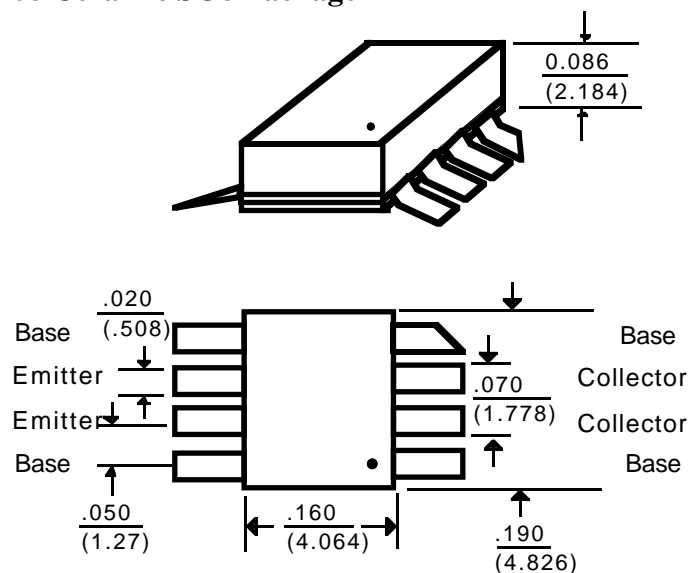
Bipolarics' B15V180 is a high performance silicon bipolar transistor intended for medium power linear and Class C applications at VHF, UHF and microwave frequencies in 7.2 and 12V systems. Depending on package type, the B15V180 can operate at up to 0.5W. These applications include high intermod receivers, CATV and instrumentation amplifiers as well as pre-drivers, drivers and final stages in transmitter applications such as cellular telephone.

Absolute Maximum Ratings:

| SYMBOL | PARAMETERS | RATING | UNITS |
|---------------|-----------------------------------|------------|------------------|
| V_{CBO} | Collector-Base Voltage | 25 | V |
| V_{CEO} | Collector-Emitter Voltage | 15 | V |
| V_{EBO} | Emitter-Base Voltage | 1.5 | V |
| I_C | Collector Current (continuous) | 240 | mA |
| $I_{C_{MAX}}$ | Collector Current (instantaneous) | 360 | mA |
| $T_J^{(1)}$ | Junction Temperature | 200 | $^\circ\text{C}$ |
| T_{STG} | Storage Temperature | -65 to 150 | $^\circ\text{C}$ |

(1) Depends on package

| SYMBOL | PARAMETERS & CONDITIONS $V_{CE} = 8V, I_C = 120 \text{ mA}$, Class A, unless stated | UNIT | MIN. | TYP. | MAX. |
|--------------|---|---------------|------|-------------|------|
| f_t | Gain Bandwidth Product | GHz | | 8.0 | |
| $ S_{21} ^2$ | Insertion Power Gain: $f = 1.0 \text{ GHz}$ $f = 2.0 \text{ GHz}$ | dB dB | | 14.2 8.2 | |
| P_{1dB} | Power output at 1dB compression: $f = 1.0 \text{ GHz}$ $I_C = 150 \text{ mA}$ | dBm | | 30.0 | |
| NF | Noise Figure: $V_{CE} = 8V, I_C = 20 \text{ mA}$ $f = 1.0 \text{ GHz}$ | dB | | 1.6 | |
| h_{FE} | Forward Current Transfer Ratio: $V_{CE} = 5V, I_C = 30 \text{ mA}$ | | 30 | 100 | 300 |
| I_{CBO} | Collector Cutoff Current : $V_{CB} = 8V$ | μA | | | 0.8 |
| C_{CB} | Collector Base Capacitance: $V_{CB} = 8V$ $f = 1 \text{ MHz}$ | pF | | .75 | |

BIPOLARICS, INC**Part Number B15V180****SILICON MICROWAVE POWER TRANSISTOR****20 0.200" Pill Package****28 0.280" Pill Package****50 Ceramic 4 Lead PAK Surface Mount****08 Ceramic SO8 Package****NOTES:** (unless otherwise specified)

- Dimensions are $\frac{\text{in}}{\text{mm}}$
- Tolerances:
in .xxx = $\pm .005$
mm .xx = $\pm .13$
- All dimensions nominal; subject to change without notice

Drawings are not to scale.

| LEAD | 1 | 2 | 3 | 4 |
|-----------------|------|---------|------|-----------|
| 20 & 28 Package | Base | Emitter | Base | Collector |